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December 2010

BSS138W

N-Channel Logic Level Enhancement Mode Field Effect Transistor

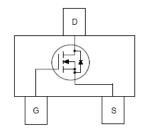
General Description

These N-Channel enhancement mode field effect transistor. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- $R_{DS(ON)} = 3.5\Omega$ @ $V_{GS} = 10V$, $I_D = 0.22A$ $R_{DS(ON)} = 6.0\Omega$ @ $V_{GS} = 4.5V$, $I_D = 0.22A$
- High density cell design for extremely low R_{DS(ON)}
- Rugged and Reliable
- Compact industry standard SOT-323 surface mount package





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{DSS}	Drain-Source Voltage	50	V
V_{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note1) - Pulsed	0.21 0.84	A A
$T_{J,}T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C
TL	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter		Parameter Value		Value	Units	
P _D	Maximum Power Dissipation Derate Above 25°C	(Note1)	340 2.72	mW mW/°C			
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	(Note1)	367	°C/W			

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
138	BSS138W	7"	8mm	3000 units

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Characteristics							
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	50			V	
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		71		mV/°C	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 50V, V_{GS} = 0V$ $V_{DS} = 50V, V_{GS} = 0V, T_{J} = 125^{\circ}C$ $V_{DS} = 30V, V_{GS} = 0V$			0.5 5 100	μA μA nA	
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			±100	nA	
On Chara	cteristics (Note2)					_	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1mA$	0.8	1.3	1.5	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 1mA, Referenced to 25°C		-3.9		mV/°C	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 0.22A$ $V_{GS} = 4.5V, I_D = 0.22A$ $V_{GS} = 10V, I_D = 0.22A, T_J = 125^{\circ}C$		1.17 1.36 2.16	3.5 6.0 5.8	Ω Ω Ω	
I _{D(ON)}	On-State Drain Current	V _{GS} = 10V, V _{DS} = 5V	0.2			Α	
9 _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 0.22A$	0.12			S	
Dynamic	Characteristics						
C _{iss}	Input Capacitance			38		pF	
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$		5.9		pF	
C _{rss}	Reverse Transfer Capacitance			3.5		pF	
R_{G}	Gate Resistance	V _{GS} = 15mV, f = 1.0MHz		11		Ω	
Switching	Characteristics (Note2)						
t _{d(on)}	Turn-On Delay Time			2.3	5	ns	
t _r	Turn-On Rise Time	$V_{DD} = 30V, I_D = 0.29A,$		1.9	18	ns	
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10V, R_{GEN} = 6\Omega$		6.7	36	ns	
t _f	Turn-Off Fall Time			6.5	14	ns	
Qg	Total Gate Change	V 25V I 0.22A		1.1		nC	
Q _{gs}	Gate-Source Change	$V_{DS} = 25V, I_{D} = 0.22A,$ $V_{GS} = 10V$		0.12		nC	
Q _{gd}	Gate-Drain Change	, vGS = 10 v		0.22		nC	
Drain-Sou	irce Diode Characteristics and	d Maximum Ratings					
I _S	Maximum Continuous Drain-Sour	ce Diode Forward Current			0.22	Α	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 0.44A$ (Note2)			1.4	V	

Notes:

- 1. 367°C/W when mounted on a minimum pad.
- **2.** Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$

Typical Performance Characteristics

Figure 1. On-Region Characteristics.

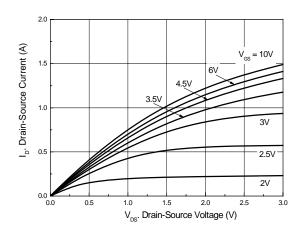


Figure 3. On-Resistance Variation with Temperature.

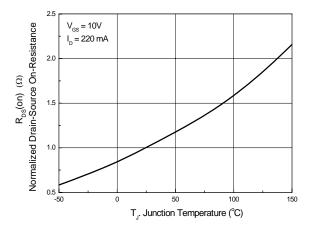


Figure 5. Drain-Source On Voltage with Temperature.

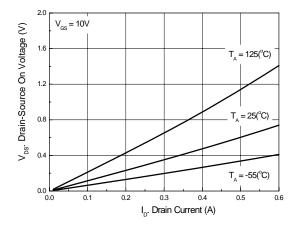


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

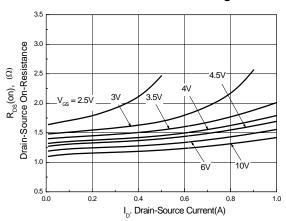


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

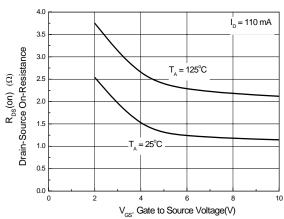
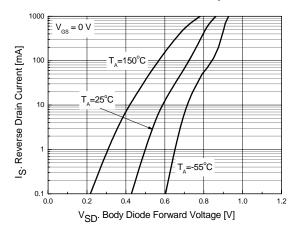


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.



Typical Performance Characteristics (Continued)

Figure 7. Gate Charge Characteristics.

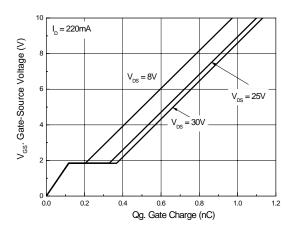


Figure 9. Maximum Safe Operating Area.

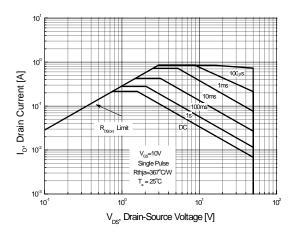


Figure 11. Transient Thermal Response Curve.

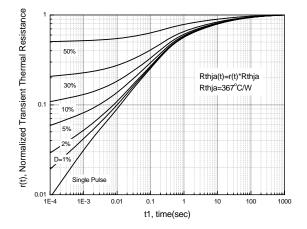


Figure 8. Capacitance Characteristics.

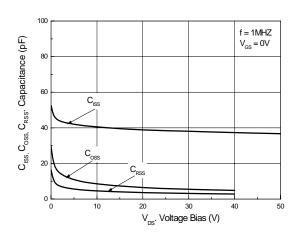
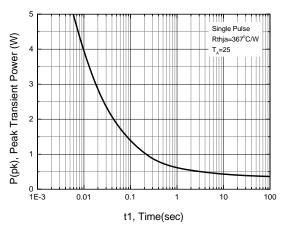
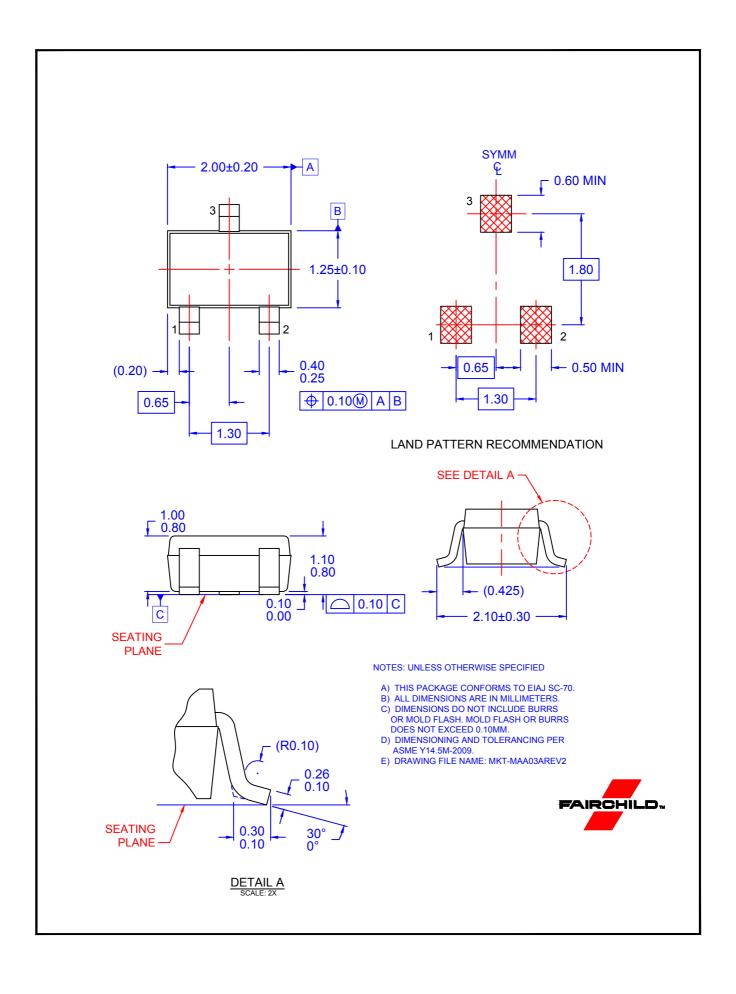


Figure 10. Single Pulse Maximum Power Dissipation.





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